

SE-514SG

1. Scope

- The specification applies to InGaN LED chips.

2. Structure

- InGaN / GaN Green LED chip.
- P Electrode (anode) : Gold
- N Electrode (cathode) : Gold

3. Size

- Chip size : 0.336 mm × 0.336 mm (13.2mil × 13.2mil).
- Pattern drawing : per fig.

4. Electro-Optical Characteristics

(Ta= +25 °C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|------------------------------|----------------|------------------------|------|------|------|------|
| Forward Voltage | V _F | I _F = 20 mA | | | 4.0 | V |
| Reverse Voltage | V _R | I _R = 10 μA | 5 | | | V |
| Radiant intensity | I _V | I _F = 20 mA | * | * | * | mcd |
| Wavelength | Hue | I _F = 20 mA | 515 | 525 | 540 | nm |
| Spectrum Width of Half Value | Δλ | I _F = 20 mA | | 30 | | nm |

規格説明：P□□□

第二碼：亮度説明 P□XX

70 ≤ A < 100mcd

100 ≤ B < 130mcd

130 ≤ C < 160mcd

160 ≤ D < 190mcd

190 ≤ E < 220mcd

220 ≤ F

第三碼：波長説明 PX□X

• 515 ≤ A < 520nm

• 520 ≤ B < 525nm

• 525 ≤ C < 530nm

• 530 ≤ D < 535nm

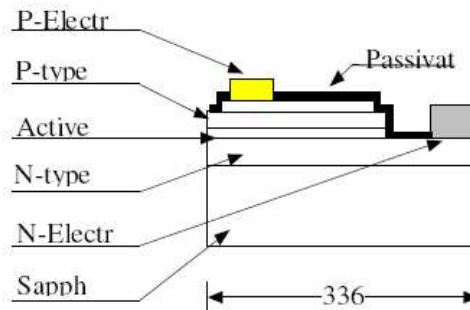
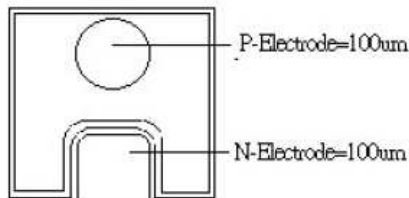
• 535 ≤ E

第四碼：説明 PXX□

◎P : With Passivation

◎O : With ITO Film

unit : μm



Chip-Thickness: 90 ± 10 μm